## THE CLAIMS

What is claimed is:

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A method for fabricating a composite substrate which method
comprises:

forming a recess in a front face of at least one of a support substrate or a source substrate that includes a zone of weakness, the recess having a configuration that, in conjunction with the zone of weakness, assists in defining a transfer layer in the source substrate;

depositing a bonding material onto at least one of the front face of the source substrate or the front face of the support substrate;

bonding the front faces of the source and support substrates together in a manner to provide at least some of the bonding material in the recess; and

detaching the transfer layer from the source substrate along the zone of weakness to form a composite substrate comprising the transfer layer, bonding material and the support substrate.

- 2. The method of claim 1 wherein transfer layer has a periphery and the configuration of the recess corresponds to the periphery of the transfer layer.
- 3. The method of claim 2 wherein the transfer layer periphery and recess are circular.
- 4. The method of claim 2 wherein the recess comprises a groove or channel.
  - 5. The method of claim 2 wherein the recess is formed in the front face of the support substrate, the bonding material is deposited onto the front face of the source substrate as a uniform layer, and the bonding material enters the recess when the source and support substrates are bonded together.
  - 6. The method of claim 2 wherein the recess is formed in the front face of the source substrate, the recess has a depth which extends to near the zone of

weakness, and the bonding material is applied onto the front face of the source substrate.

- 7. The method of claim 6 wherein the recess is configured to receive bonding material so that the bonding material does not extend past the zone of weakness on outer portions of the source substrate.
  - 8. The method of claim 6 wherein the bonding material in the recess protects the peripheral edge of the transfer layer.

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- 9. The method of claim 1 wherein the recess is formed through the entire thickness of the source substrate or the support substrate.
- 10. The method of claim 1 wherein recesses are formed through the entire thickness of both the source substrate and the support substrate.
  - 11. The method of claim 1 wherein the bonding material is releasable.
- 12. The method of claim 1 wherein the recess is formed by at least one of wet etching or dry etching.
  - 13. The method of claim 1 wherein the recess is formed by mechanical machining.
- 14. The method of claim 13 wherein the mechanical machining is conducted using at least one of a saw or a laser beam.
  - 15. The method of claim 1 which further comprises implanting atomic species into the source substrate to form the zone of weakness.
  - 16. The method of claim 15 which further comprises forming the recess in the source substrate prior to implanting the atomic species.

- 17. The method of claim 1 which further comprises providing a porous layer in the source substrate to form the zone of weakness.
- 18. The method of claim 1 which further comprises providing a releasable bonding interface to form the zone of weakness.
  - 19. The method of claim 1 wherein the transfer layer is detached by applying a mechanical stress to the zone of weakness.
- 10 20. The method of claim 19 wherein the mechanical stress includes at least one of a tension, a bending stress or a shear stress.
  - 21. The method of claim 1 wherein the transfer layer comprises a semiconductor material.

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- 22. The method of claim 1 wherein the bonding material comprises an adhesive or adhesive material.
- 23. A composite substrate comprising a transfer layer, bonding material and the support substrate, wherein the bonding material is present in a recess having a configuration that assists in defining the transfer layer and as a layer that bonds the transfer layer to the support substrate.
- 24. The composite substrate of claim 23, wherein the transfer layer comprises a semiconductor material and the bonding material comprises an adhesive or adhesive material.
  - 25. The composite substrate of claim 23 wherein transfer layer has a circular periphery and the recess has a circular configuration.

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